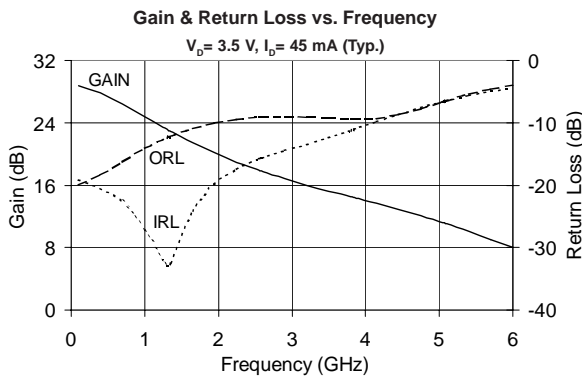




Product Description

The SGA-4563 is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring 1 micron emitters provides high F_T and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only 2 DC-blocking capacitors, a bias resistor and an optional RF choke are required for operation.

The matte tin finish on Sirenza's lead-free package utilizes a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU Directive 2002/95. This package is also manufactured with green molding compounds that contain no antimony trioxide nor halogenated fire retardants. blocking capacitors, a bias resistor and an optional RF choke are required for operation.



| Symbol | Parameter | Units | Frequency | Min. | Typ. | Max. |
|-------------------------|---------------------------------------|--|---|--|----------------------|------|
| G | Small Signal Gain | dB | 850 MHz 1950 MHz 2400 MHz | | 25.6 20.2 18.6 | |
| P_{1dB} | Output Power at 1dB Compression | dBm | 850 MHz 1950 MHz | | 15.0 12.8 | |
| OIP_3 | Output Third Order Intercept Point | dBm | 850 MHz 1950 MHz | | 27.1 26.2 | |
| Bandwidth | Determined by Return Loss (>10dB) | MHz | | | 2500 | |
| IRL | Input Return Loss | dB | 1950 MHz | | 19.9 | |
| ORL | Output Return Loss | dB | 1950 MHz | | 10.1 | |
| NF | Noise Figure | dB | 1950 MHz | | 2.4 | |
| V_D | Device Operating Voltage | V | | | 3.6 | |
| I_D | Device Operating Current | mA | | 41 | 45 | 49 |
| $R_{TH}, j-l$ | Thermal Resistance (junction to lead) | $^{\circ}\text{C}/\text{W}$ | | | 255 | |
| Test Conditions: | | $V_S = 8\text{ V}$ $R_{BIAS} = 100\text{ Ohms}$ | $I_D = 45\text{ mA Typ.}$ $T_L = 25^{\circ}\text{C}$ | OIP_3 Tone Spacing = 1 MHz, P_{out} per tone = -10 dBm $Z_S = Z_L = 50\text{ Ohms}$ | | |

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SGA-4563

SGA-4563Z



DC-2500 MHz, Cascadable SiGe HBT MMIC Amplifier



Product Features

- Now available in Lead Free, RoHS Compliant, & Green Packaging
- High Gain : 20.2 dB at 1950 MHz
- Cascadable 50 Ohm
- Operates From Single Supply
- Low Thermal Resistance Package

Applications

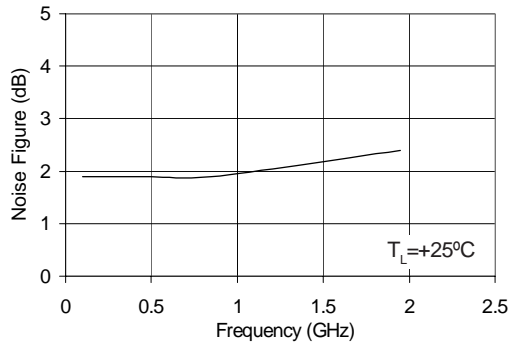
- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

Typical RF Performance at Key Operating Frequencies

| Symbol | Parameter | Unit | Frequency (MHz) | | | | | |
|------------------|------------------------------------|------|-----------------|------|------|------|------|------|
| | | | 100 | 500 | 850 | 1950 | 2400 | 3500 |
| G | Small Signal Gain | dB | 28.7 | 27.4 | 25.6 | 20.2 | 18.6 | 15.3 |
| OIP ₃ | Output Third Order Intercept Point | dBm | 27.0 | 26.2 | 27.1 | 26.2 | 25.3 | |
| P _{1dB} | Output Power at 1dB Compression | dBm | 15.7 | 15.0 | 15.0 | 12.8 | 11.6 | |
| IRL | Input Return Loss | dB | 19.2 | 20.7 | 24.5 | 19.9 | 16.5 | 12.4 |
| ORL | Output Return Loss | dB | 20.0 | 17.7 | 15.0 | 10.1 | 9.3 | 9.3 |
| S ₁₂ | Reverse Isolation | dB | 30.5 | 29.7 | 28.7 | 24.5 | 23.0 | 19.9 |
| NF | Noise Figure | dB | 1.9 | 1.9 | 1.9 | 2.4 | | |

Test Conditions: V_S = 8 V, I_D = 45 mA Typ., OIP₃ Tone Spacing = 1 MHz, P_{out} per tone = -10 dBm
R_{BIAS} = 100 Ohms, T_L = 25°C, Z_S = Z_L = 50 Ohms

Noise Figure vs. Frequency
V_D = 3.5 V, I_D = 45 mA (Typ.)

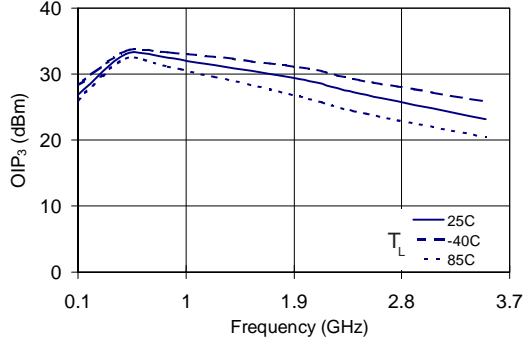


Absolute Maximum Ratings

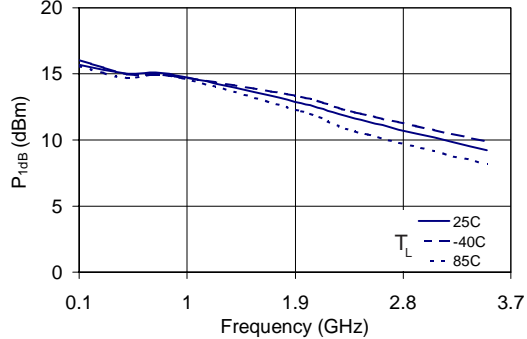
| Parameter | Absolute Limit |
|---|----------------|
| Max. Device Current (I _D) | 90 mA |
| Max. Device Voltage (V _D) | 6 V |
| Max. RF Input Power | +18 dBm |
| Max. Junction Temp. (T _J) | +150°C |
| Operating Temp. Range (T _L) | -40°C to +85°C |
| Max. Storage Temp. | +150°C |

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.
Bias conditions should also satisfy the following expression:
 $I_D V_D < (T_J - T_L) / R_{TH} \text{ J}^{-1}$

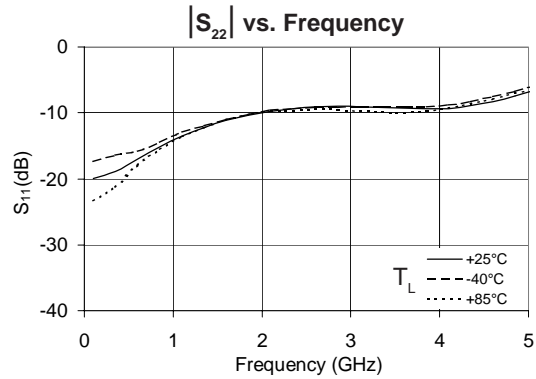
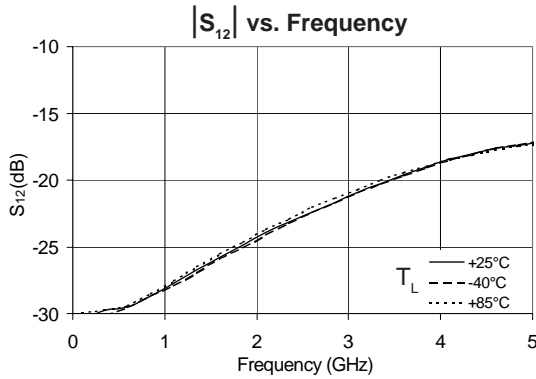
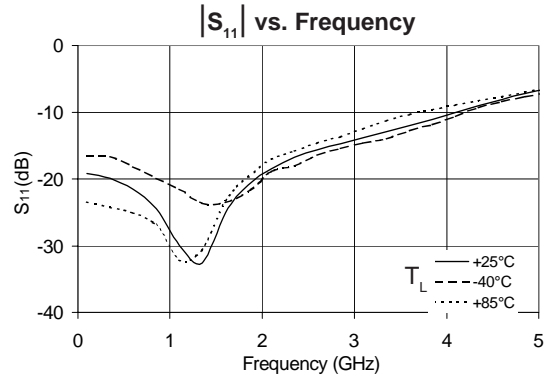
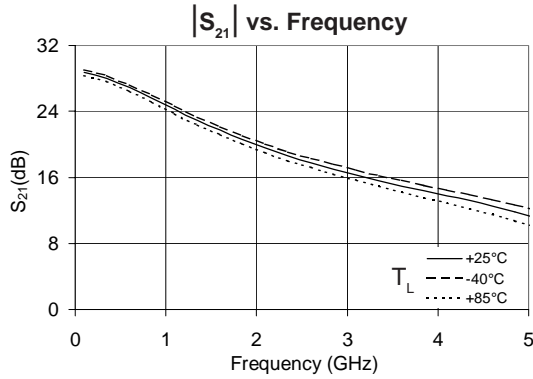
OIP₃ vs. Frequency
V_D = 3.5 V, I_D = 45 mA (Typ.)



P_{1dB} vs. Frequency
V_D = 3.5 V, I_D = 45 mA (Typ.)

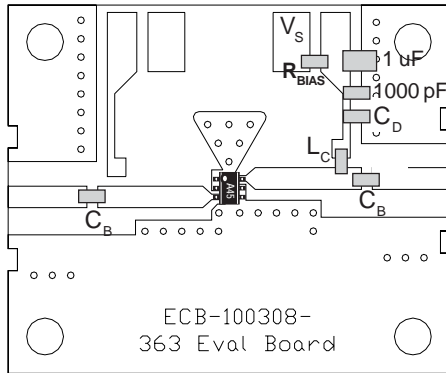
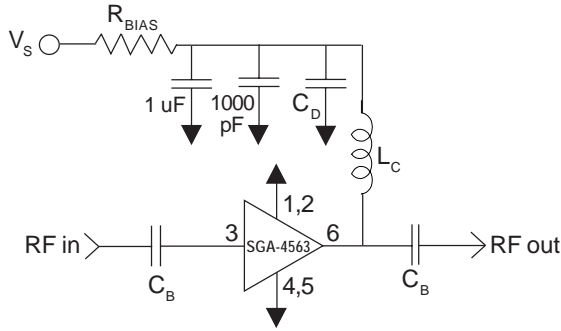


Typical RF Performance Over Temperature (Bias: $V_D = 3.5\text{ V}$, $I_D = 45\text{ mA}$ (Typ.))

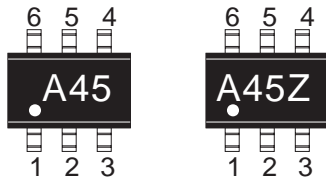


NOTE: Full S-parameter data available at www.sirenza.com

Basic Application Circuit



Part Identification Marking



Caution: ESD sensitive
Appropriate precautions in handling, packaging and testing devices must be observed.

Application Circuit Element Values

| Reference Designator | Frequency (Mhz) | | | | |
|----------------------|-----------------|--------|-------|-------|-------|
| | 500 | 850 | 1950 | 2400 | 3500 |
| C _B | 220 pF | 100 pF | 68 pF | 56 pF | 39 pF |
| C _D | 100 pF | 68 pF | 22 pF | 22 pF | 15 pF |
| L _C | 68 nH | 33 nH | 22 nH | 18 nH | 15 nH |

Recommended Bias Resistor Values for I_D=45mA

$$R_{BIAS} = (V_S - V_D) / I_D$$

| Supply Voltage (V _S) | 6 V | 8 V | 10 V | 12 V |
|----------------------------------|------|-------|-------|-------|
| R _{BIAS} | 51 Ω | 100 Ω | 150 Ω | 180 Ω |

Note: R_{BIAS} provides DC bias stability over temperature.

Mounting Instructions

1. Use a large ground pad area near device pins 1, 2, 4, and 5 with many plated through-holes as shown.
2. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

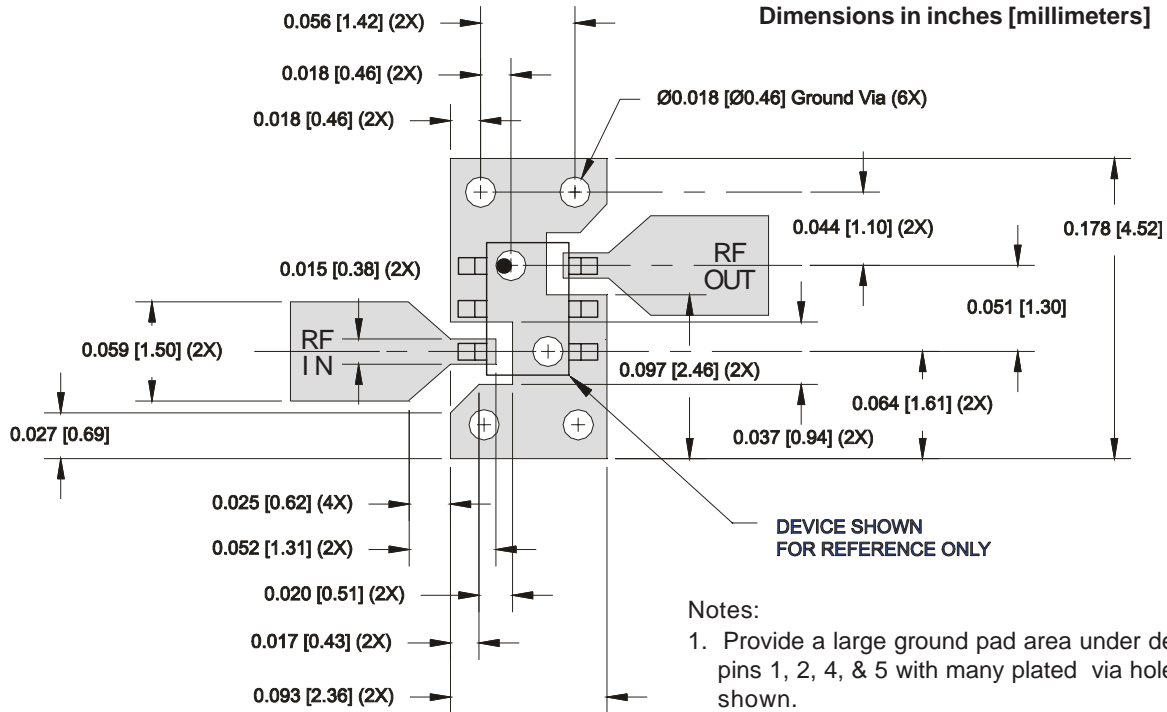
| Pin # | Function | Description |
|------------|-------------|---|
| 3 | RF IN | RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation. |
| 1, 2, 4, 5 | GND | Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible. |
| 6 | RF OUT/BIAS | RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation. |

Part Number Ordering Information

| Part Number | Reel Size | Devices/Reel |
|-------------|-----------|--------------|
| SGA-4563 | 7" | 3000 |
| SGA-4563Z | 7" | 3000 |

SOT-363 PCB Pad Layout

Dimensions in inches [millimeters]



DEVICE SHOWN FOR REFERENCE ONLY

Notes:

1. Provide a large ground pad area under device pins 1, 2, 4, & 5 with many plated via holes as shown.
2. Dimensions given for 50 Ohm RF I/O lines are for 31 mil thick Getek. Scale accordingly for different board thicknesses and dielectric constants.
3. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick Getek with 1 ounce copper on both sides.

SOT-363 Nominal Package Dimensions

Dimensions in inches [millimeters]

A link to the SOT-363 package outline drawing with full dimensions and tolerances may be found on the product web page at www.sirenza.com.

